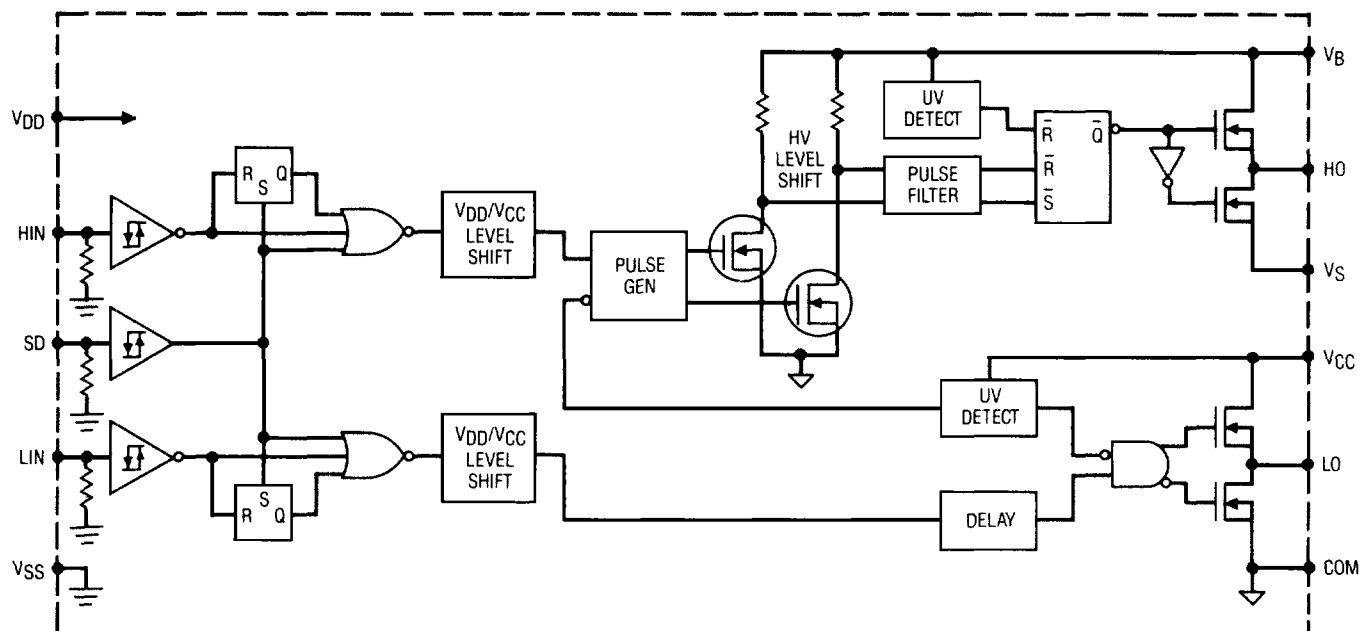
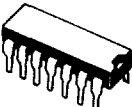
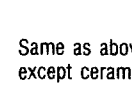




High Voltage MOS Gate Driver IR2110



FEATURES

- Drives a pair of HEXFETs or IGBTs
- Two Independent Channel Drivers
 - One Floating High Side Driver
 - One Ground Referenced Low Side Driver
- Operates to 500V
- 2 Amperes Peak Current Drive Capability
- Operates to 500 KHz
- High dv/dt ($> \pm 50\text{V/ns}$) Immunity
- CMOS and LSTTL Compatible Schmitt Trigger Inputs
- Low Quiescent Power Dissipation
- Undervoltage Lockout with Hysteresis (both channels)
- 25 ns Typical Switching Time (into 100 pf load)
- Matched Delay Times for Both Channels (within 10 ns)
 - 120 ns Turn-on Delay
 - 94 ns Turn-off Delay
- Cycle by Cycle Edged Triggered Latched Shutdown
- Logic Supply Return Can Swing $\pm 5\text{V}$ from Power Ground
- Floating Supply Offset -5V from Power Ground
- Latch Immune CMOS (withstands $> 2\text{A}$ reverse current at I/O pins)

PART NUMBER	V _S OFFSET SUPPLY VOLTAGE (V)	V _{BS} , V _{CC} OUTPUT VOLTAGE (V)	I _{OUT} SINK, SOURCE (A)	CASE/DIE OUTLINE NO. (4)	NOTES	CASE STYLE
IR2110	10-500	10-20	2	P2	—	14 PIN PLASTIC 
IR2110L	10-500	10-20	2	P3	—	14 PIN CERAMIC MO-036AB  Same as above except ceramic
IR2110C	10-500	10-20	2	P4	(2)	DIE 
IR2110S	10-500	10-20	2	P5	(1)	16 PIN WIDE BODY SURFACE MOUNT 
IR2119	10-500	10-20	2	—	(3)	DESIGNER'S KIT IN 9 x 12 x 1" VELCRO BOX

- (1) — Consult factory for minimum order quantity.
 (2) — Provided in waffle pack, 100 die to a pack.
 (3) — For Kit Information and contents see page 8.
 (4) — For case outline drawing see page 132.